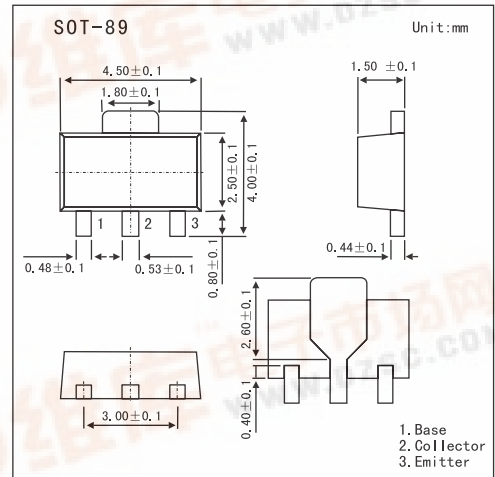


SMD Type Transistors

Small Signal Transistor  
2SC5211

Features

- High voltage  $V_{CE0}=50V$ .
- Small package for mounting.



Absolute Maximum Ratings  $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	55	V
Emitter-base voltage	$V_{EB0}$	4	V
Collector-emitter voltage	$V_{CE0}$	50	V
Peak collector current	$I_{CM}$	600	mA
Collector current	$I_C$	400	mA
Collector dissipation	$P_C$	500	mW
Junction temperature	$T_j$	150	$^{\circ}C$
Storage temperature	$T_{stg}$	-55 to +150	$^{\circ}C$

Electrical Characteristics  $T_a = 25^{\circ}C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	55			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	4			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=100\mu A, R_{BE}=\infty$	50			V
Collector cutoff current	$I_{CBO}$	$V_{CB}=25V, I_E=0$			1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=2V, I_C=0$			1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=4V, I_C=100mA$	90		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=10mA$		0.15	0.5	V
Gain bandwidth product	$f_T$	$V_{CE}=6V, I_E=-10mA$		150		MHz

hFE Classification

Marking	TD	TE	TF
	90~180	150~300	250~500

